

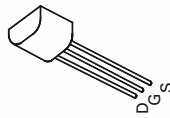
**P-CHANNEL ENHANCEMENT
MODE VERTICAL DMOS FET**

ISSUE 2 – MARCH 94

FEATURES

- * 200 Volt V_{DS}
- * $R_{DS(on)}=32\Omega$

ZVP0120A



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

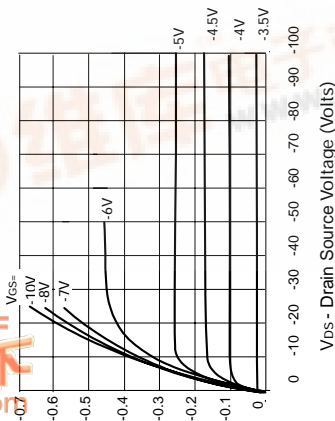
PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	-200	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	-110	mA
Pulsed Drain Current	I_{DM}	-1	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	700	mW
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

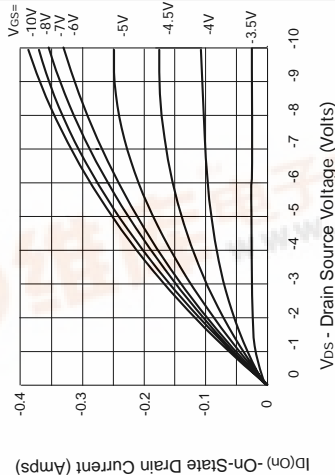
PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	-200		V	$I_D=-1mA, V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.5	-3.5	V	$I_D=-1mA, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		20	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}		-10 -100	μA μA	$V_{DS}=-200V, V_{GS}=0$ $V_{DS}=-160V, V_{GS}=0V,$ $T=125^{\circ}C(2)$
On-State Drain Current(1)	$I_{D(on)}$	-250		mA	$V_{DS}=-25V, V_{GS}=-10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		32	Ω	$V_{GS}=-10V, I_D=-125mA$
Forward Transconductance (1)(2)	g_{fs}	50		mS	$V_{DS}=-25V, I_D=-125mA$
Input Capacitance (2)	C_{iss}		100	pF	
Common Source Output Capacitance (2)	C_{oss}		25	pF	$V_{DS}=-25V, V_{GS}=0V, f=1MHz$
Reverse Transfer Capacitance (2)	C_{rss}		7	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		7	ns	
Rise Time (2)(3)	t_r		15	ns	$V_{DD}=-25V, I_D=-125mA$
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		12	ns	
Fall Time (2)(3)	t_f		15	ns	

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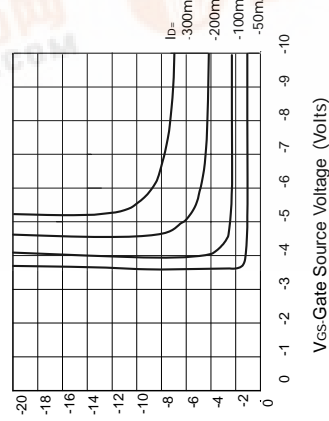
TYPICAL CHARACTERISTICS



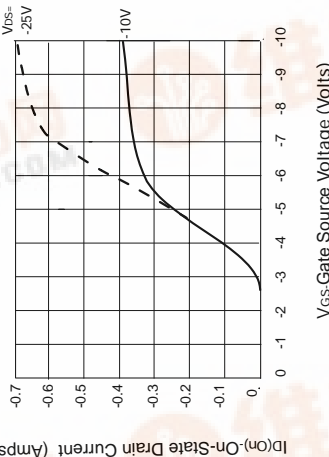
Output Characteristics



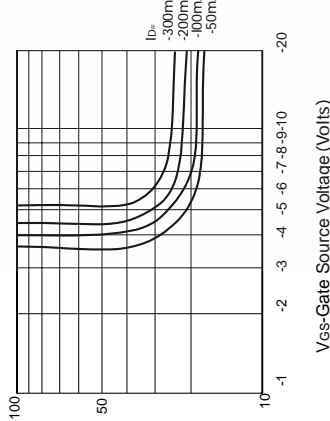
Saturation Characteristics



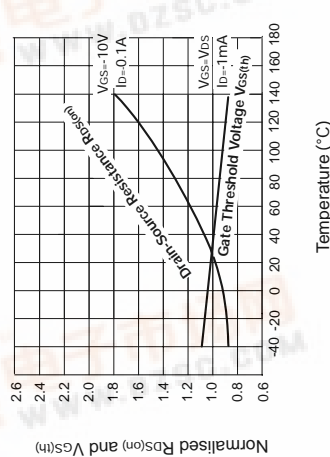
Voltage Saturation Characteristics



Transfer Characteristics



On-resistance vs gate-source voltage



Normalised $R_{DS(on)}$ and $V_{GS(th)}$ vs Temperature

P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

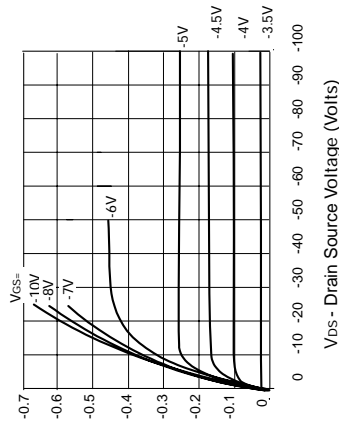
ISSUE 2 – MARCH 94

FEATURES

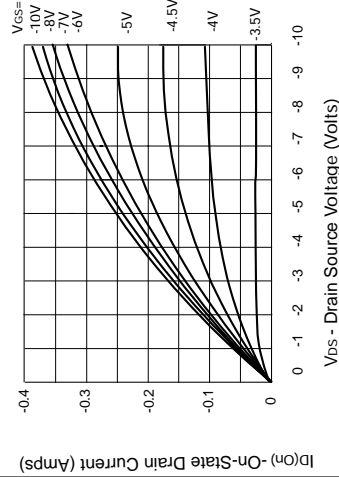
- * 200 Volt V_{DS}
- * $R_{DS(on)}=32\Omega$

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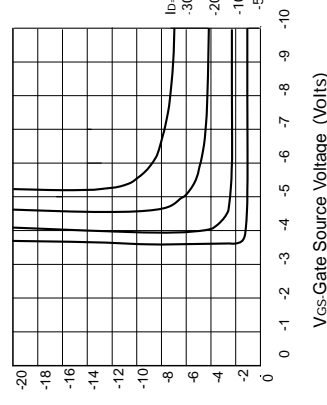
TYPICAL CHARACTERISTICS



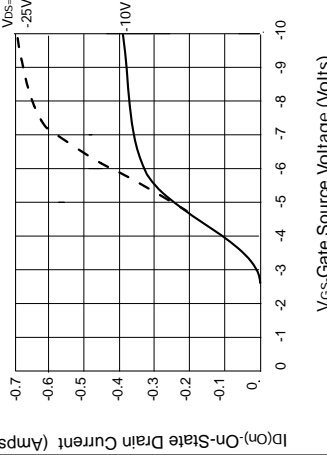
Output Characteristics



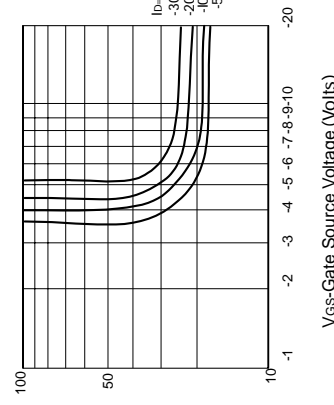
Saturation Characteristics



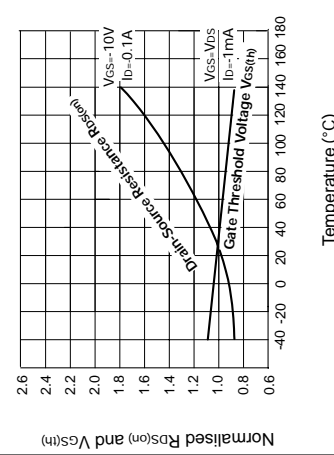
Voltage Saturation Characteristics



Transfer Characteristics



On-resistance vs gate-source voltage



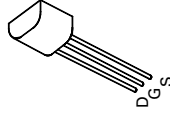
Normalised $R_{DS(on)}$ and $V_{GS(th)}$ vs Temperature

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	-200	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	-110	mA
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Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	-200		V	$I_D = -1mA, V_{GS} = 0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.5	-3.5	V	$I_D = -1mA, V_{DS} = V_{GS}$
Gate-Body Leakage	I_{GSS}		20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Zero Gate Voltage Drain Current	I_{DSS}		-10 -100	μA μA	$V_{DS} = -200V, V_{GS} = 0$ $V_{DS} = -160V, V_{GS} = 0V, T = 125^{\circ}C(2)$
On-State Drain Current(1)	$I_{D(on)}$	-250		mA	$V_{DS} = -25V, V_{GS} = -10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		32	Ω	$V_{GS} = -10V, I_D = -125mA$
Forward Transconductance (1)(2)	g_{fs}	50		mS	$V_{DS} = -25V, I_D = -125mA$
Input Capacitance (2)	C_{iss}		100	pF	
Common Source Output Capacitance (2)	C_{oss}		25	pF	$V_{DS} = -25V, V_{GS} = 0V, f = 1MHz$
Reverse Transfer Capacitance (2)	C_{rss}		7	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		7	ns	
Rise Time (2)(3)	t_r		15	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		12	ns	
Fall Time (2)(3)	t_f		15	ns	$V_{DD} = -25V, I_D = -125mA$

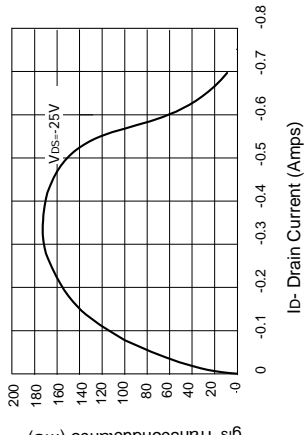


E-Line
TO92 Compatible

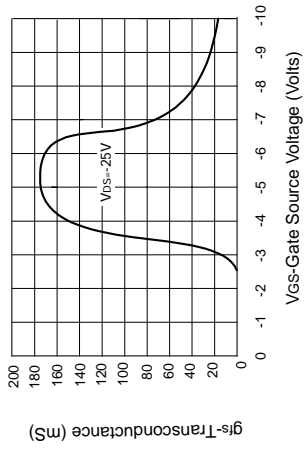
Measured under pulsed conditions. $W_{width} = 300\mu s$. Duty cycle $\leq 2\%$. (2) Sample test.

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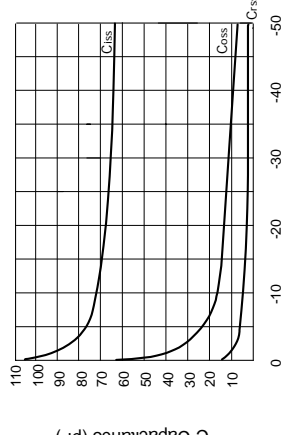
TYPICAL CHARACTERISTICS



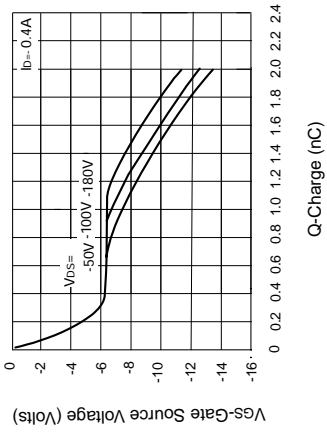
Transconductance v drain current



Transconductance v gate-source voltage



Capacitance v drain-source voltage



Gate charge v gate-source voltage